

**1. Scope :**

This specification applies to PIN silicon photodiode chips,  
Device No. PD-30092-B.

**2. Structure :**

- 2-1. Type : PIN diode.
- 2-2. Electrodes :  
Top side( Anode ) : Aluminum alloy.  
Back side ( Cathode ) : Gold.

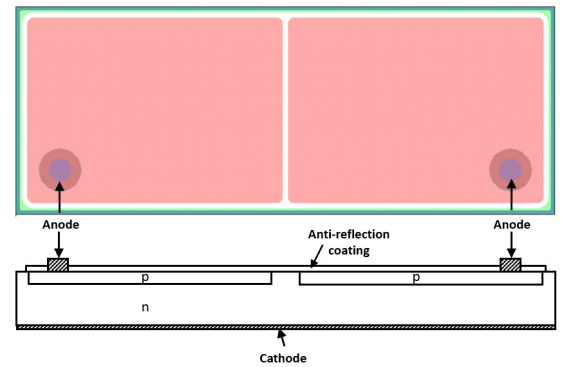
**3. Size :**

- 3-1. Chip size (including scribe lane) : 149.6 mils x 57.4 mils (3.8 mm x 1.46 mm ).
- 3-2. Chip thickness :  $12 \pm 1.0$  mils (  $0.305 \pm 0.025$  mm).
- 3-3. Active area : 70.8 mils x 51.1 mils x 2 (1.8 mm x 1.3 mm ).
- 3-4. Bonding pad (Anode) :  $11.81 \pm 0.394$  mils (  $0.30 \pm 0.010$  mm ) Diameter
- 3-5. Pattern drawing : Refer to the attached drawing.

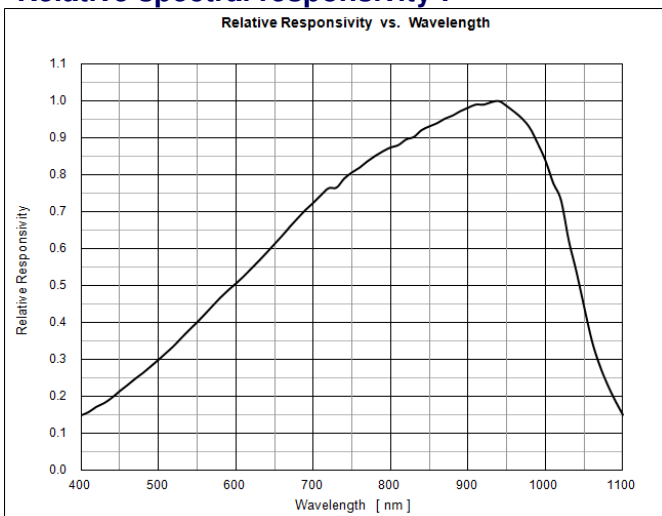
**4. Electrical characteristics (Ta = 25 °C) :**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse dark current	$I_D$	$V_R=10V$ $E_e=0mW/cm^2$			5	nA
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$ $E_e=0mW/cm^2$	60			V
Forward Voltage	$V_F$	$I_F=10mA$ $E_e=0mW/cm^2$			1.3	V
Sensitivity	S	$V_R=5V$ $\lambda=940nm$		0.6		A/W

\*Based on 100% probing



**5. Relative spectral responsivity :**



\*bare chip measured with integrating sphere, for reference only.